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# 1SS199

Silicon Schottky Barrier Diode for Various Detector,  
High Speed Switching

## HITACHI

ADE-208-299A (Z)  
Rev. 1

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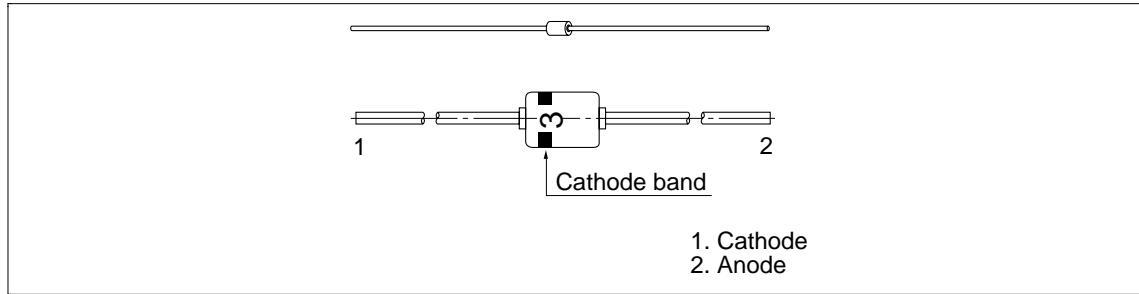
### Features

- Detection efficiency is very good.
- Small temperature coefficient.
- Small glass package (MHD) enables easy mounting and high reliability.

### Ordering Information

Type No.	Cathode band	Mark	Package Code
1SS199	Green	3	MHD

### Outline



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## 1SS199

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### Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Value	Unit
Reverse voltage	V <sub>R</sub>	30	V
Average rectified current	I <sub>o</sub>	15	mA
Junction temperature	T <sub>j</sub>	125	°C
Storage temperature	T <sub>stg</sub>	-55 to +125	°C

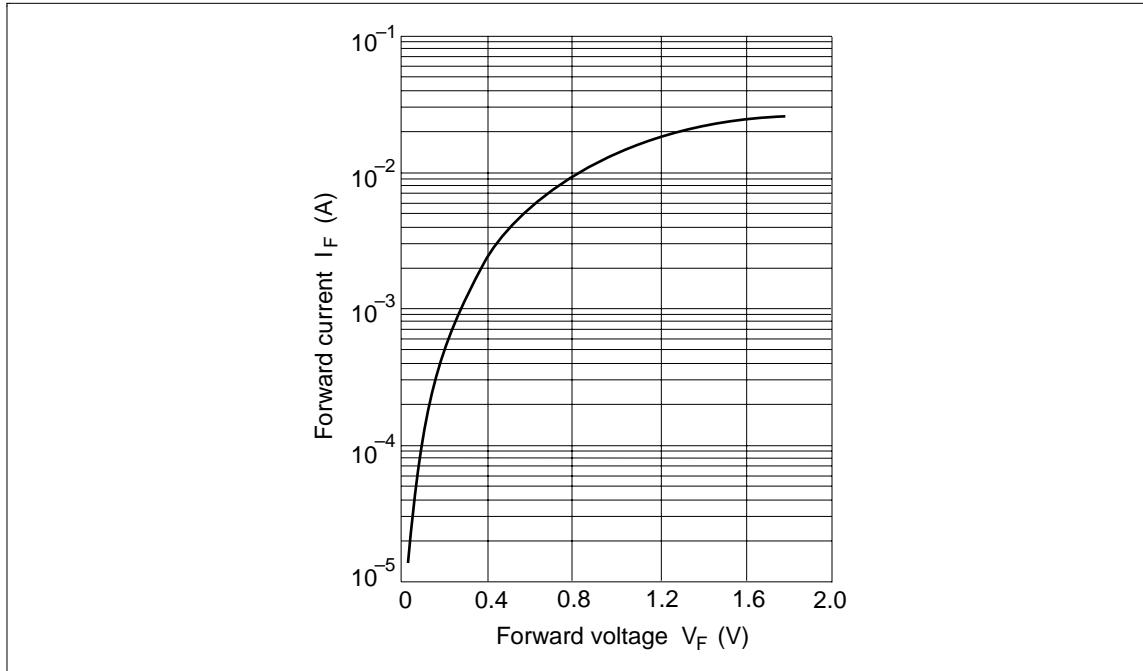
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### Electrical Characteristics (Ta = 25°C)

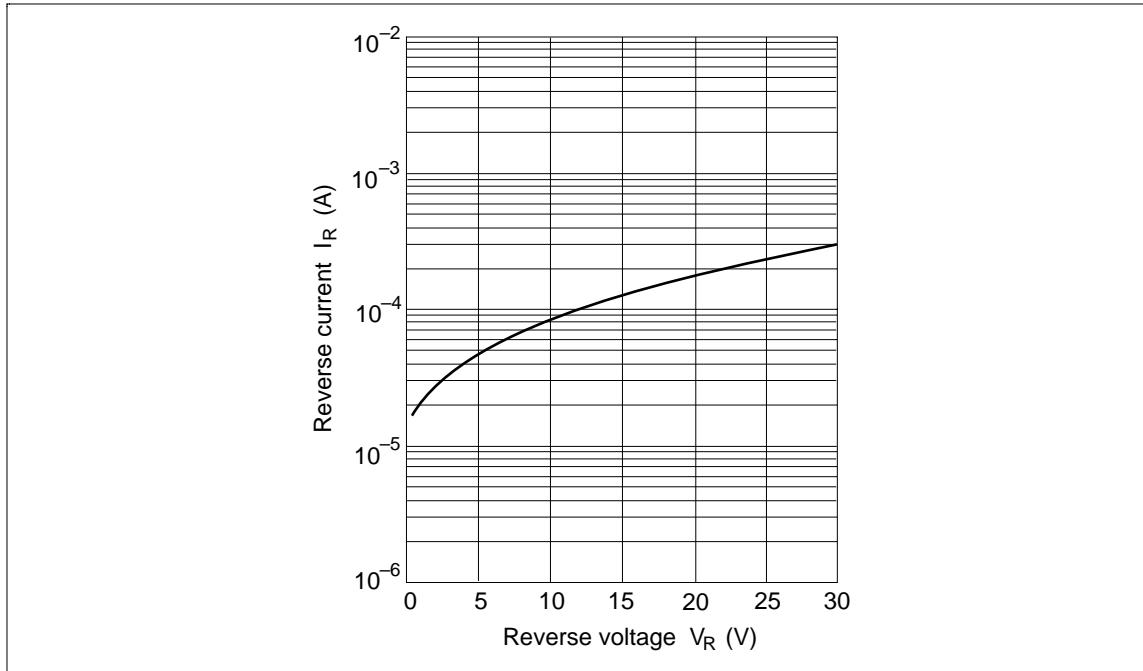
Item	Symbol	Min	Typ	Max	Unit	Test Condition
Forward current	I <sub>F</sub>	3.0	—	—	mA	V <sub>F</sub> = 1V
Reverse current	I <sub>R</sub>	—	—	100	µA	V <sub>R</sub> = 10V
Capacitance	C	—	—	3.0	pF	V <sub>R</sub> = 1V, f = 1MHz
Rectifier efficiency	η	70	—	—	%	V <sub>in</sub> = 2Vrms, f = 40MHz, R <sub>L</sub> = 5kΩ, C <sub>L</sub> = 20pF
ESD-Capability	—	70	—	—	V	*C = 200pF, Both forward and reverse direction 1 pulse.

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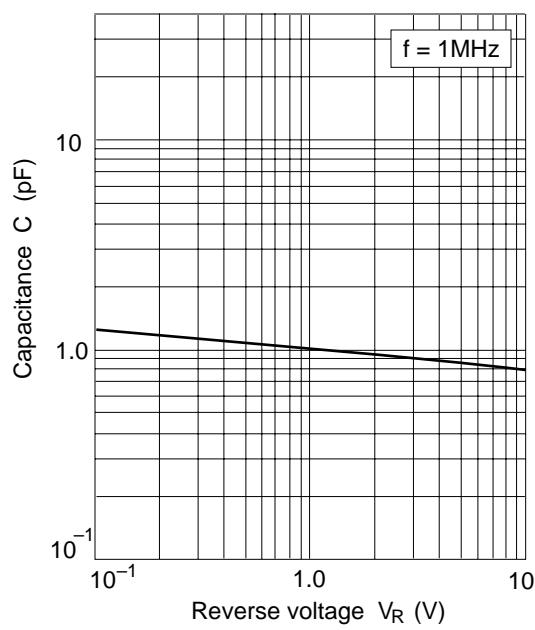
Note: Failure criterion; I<sub>R</sub> ≥ 200µA at V<sub>R</sub> = 10V



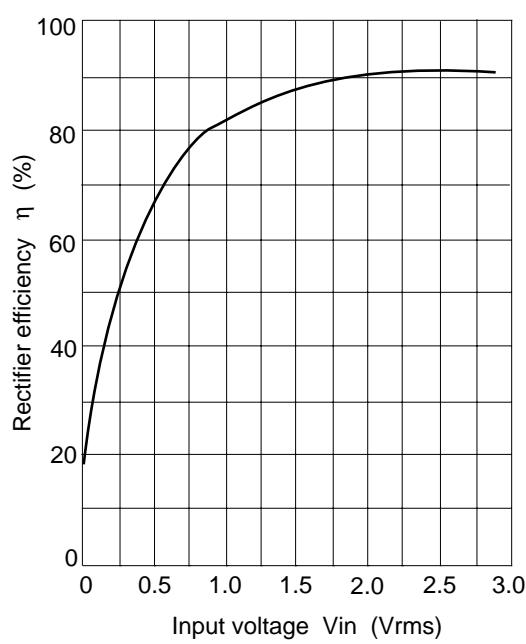
**Fig.1** Forward current Vs. Forward voltage



**Fig.2** Reverse current Vs. Reverse voltage



**Fig.3 Capacitance Vs. Reverse voltage**



**Fig.4 Rectifier efficiency Vs. Input voltage**

**Package Dimensions**